
HD74ALVC16244

16-bit Buffer / Driver with 3-state Outputs

HITACHI

ADE-205-206 (Z)
Preliminary
1st. Edition
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Description

This 16-bit buffer / driver is designed for 2.3 V to 3.6 V V_{CC} operation.

The HD74ALVC16244 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce $< 0.8 \text{ V}$ ($@V_{CC} = 3.3 \text{ V}$, $T_a = 25^\circ\text{C}$)
- Typical V_{OH} undershoot $> 2.0 \text{ V}$ ($@V_{CC} = 3.3 \text{ V}$, $T_a = 25^\circ\text{C}$)
- High output current $\pm 24 \text{ mA}$ ($@V_{CC} = 3.0 \text{ V}$)

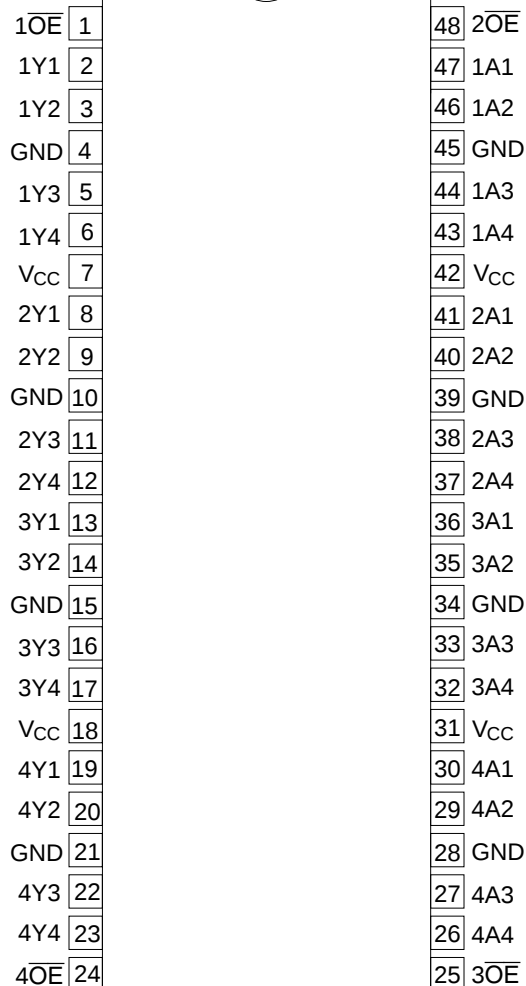
HD74ALVC16244

Function Table

Inputs		Output Y
OE	A	
L	H	H
L	L	L
H	X	Z

H : High level
L : Low level
X : Immaterial
Z : High impedance

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	−0.5 to 4.6	V	
Input voltage ^{*1}	V_I	−0.5 to 4.6	V	
Output voltage ^{*1, 2}	V_O	−0.5 to $V_{CC} + 0.5$	V	
Input clamp current	I_{IK}	−50	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±50	mA	$V_O = 0$ to V_{CC}
V_{CC} , GND current / pin	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at $T_a = 55^{\circ}\text{C}$ (in still air) ^{*3}	P_T	0.85	W	TSSOP
Storage temperature	T_{stg}	−65 to 150	$^{\circ}\text{C}$	

Notes: Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

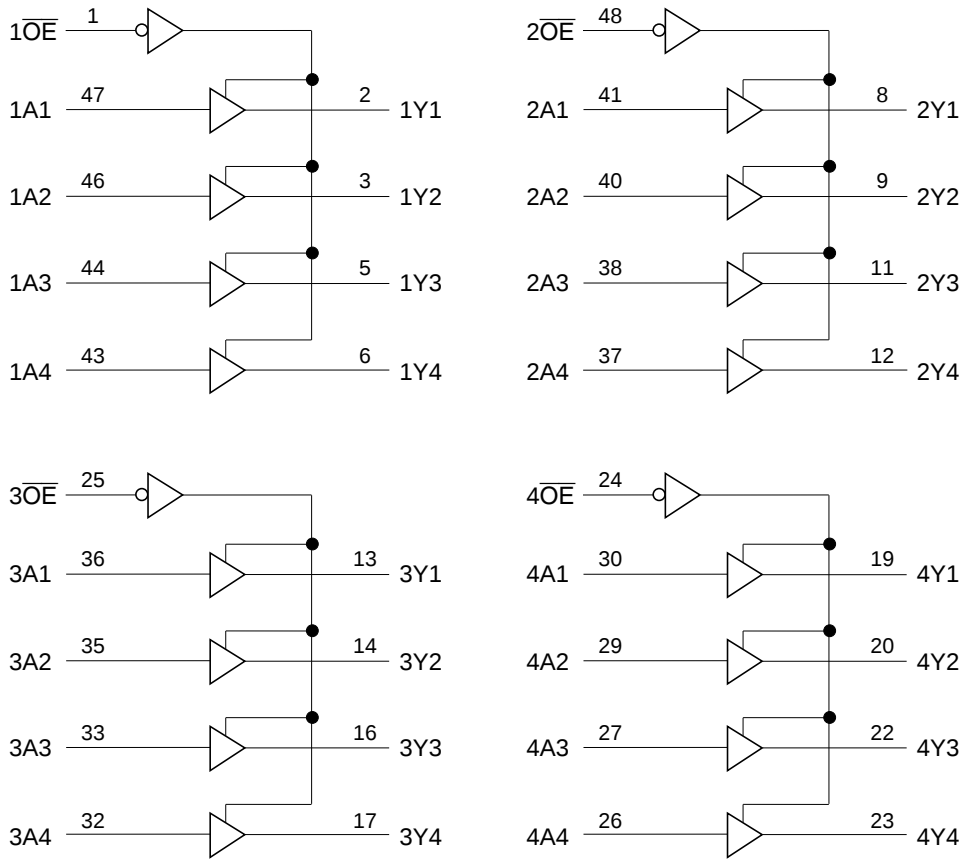
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150 $^{\circ}\text{C}$ and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V_{CC}	2.3	3.6	V	
Input voltage	V_I	0	V_{CC}	V	
Output voltage	V_O	0	V_{CC}	V	
High level output current	I_{OH}	—	−12	mA	$V_{CC} = 2.3\text{ V}$
		—	−12		$V_{CC} = 2.7\text{ V}$
		—	−24		$V_{CC} = 3.0\text{ V}$
Low level output current	I_{OL}	—	12	mA	$V_{CC} = 2.3\text{ V}$
		—	12		$V_{CC} = 2.7\text{ V}$
		—	24		$V_{CC} = 3.0\text{ V}$
Input transition rise or fall rate	$\Delta t / \Delta v$	0	10	ns / V	
Operating temperature	T_a	−40	85	$^{\circ}\text{C}$	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



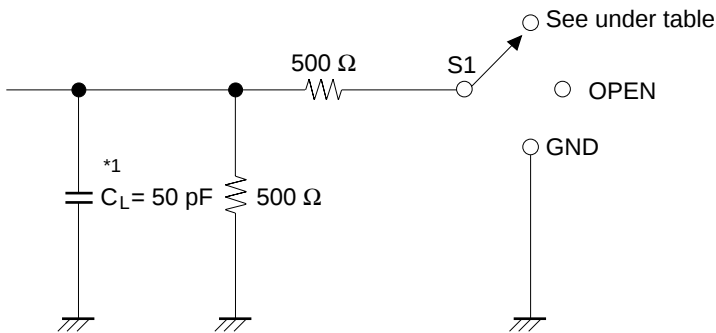
Electrical Characteristics (Ta = -40 to 85°C)

	Symbo	V _{CC} (V)	Min	Max	Unit	Test Conditions
	I					
Input voltage	V _{IH}	2.3 to 2.7	1.7	—	V	
		2.7 to 3.6	2.0	—		
	V _{IL}	2.3 to 2.7	—	0.7		
		2.7 to 3.6	—	0.8		
Output voltage	V _{OH}	2.3 to 3.6	V _{CC} -0.2	—	V	I _{OH} = -100 μA
		2.3	2.0	—		I _{OH} = -6 mA, V _{IH} = 1.7 V
		2.3	1.7	—		I _{OH} = -12 mA, V _{IH} = 1.7 V
		2.7	2.2	—		I _{OH} = -12 mA, V _{IH} = 2.0 V
		3.0	2.4	—		I _{OH} = -12 mA, V _{IH} = 2.0 V
		3.0	2.0	—		I _{OH} = -24 mA, V _{IH} = 2.0 V
	V _{OL}	2.3 to 3.6	—	0.2		I _{OL} = 100 μA
		2.3	—	0.4		I _{OL} = 6 mA, V _{IL} = 0.7 V
		2.3	—	0.7		I _{OL} = 12 mA, V _{IL} = 0.7 V
		2.7	—	0.4		I _{OL} = 12 mA, V _{IL} = 0.8 V
		3.0	—	0.55		I _{OL} = 24 mA, V _{IL} = 0.8 V
Input current	I _{IN}	3.6	—	±5	μA	V _{IN} = V _{CC} or GND
Off state output current	I _{OZ}	3.6	—	±10	μA	V _{OUT} = V _{CC} or GND
Quiescent supply current	I _{CC}	3.6	—	40	μA	V _{IN} = V _{CC} or GND
	ΔI _{CC}	3.0 to 3.6	—	750	μA	V _{IN} = one input at (V _{CC} -0.6) V, other inputs at V _{CC} or GND

Switching Characteristics (Ta = -40 to 85°C)

Item	Symbol	V _{CC} (V)	Min	Typ	Max	Unit	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH}	2.5±0.2	1.0	—	3.7	ns	A	Y
	t _{PHL}	2.7	—	—	3.6			
		3.3±0.3	1.0	—	3.0			
Output enable time	t _{ZH}	2.5±0.2	1.0	—	5.7	ns	$\overline{OE}$	Y
	t _{ZL}	2.7	—	—	5.4			
		3.3±0.3	1.0	—	4.4			
Output disable time	t _{HZ}	2.5±0.2	1.0	—	5.2	ns	$\overline{OE}$	Y
	t _{LZ}	2.7	—	—	4.6			
		3.3±0.3	1.0	—	4.1			
Input capacitance	C _{IN}	3.3	—	3.0	—	pF	Control inputs	
		3.3	—	6.0	—		Data inputs	
Output capacitance	C _O	3.3	—	7.0	—	pF	Outputs	

Test Circuit

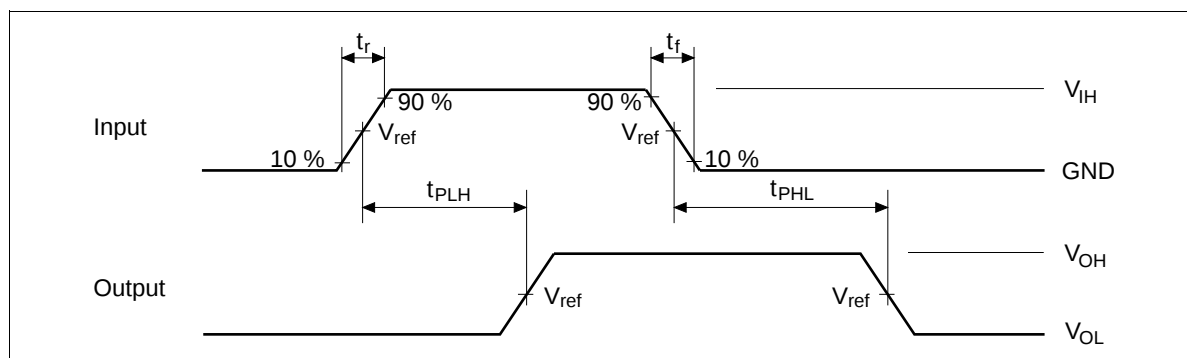


Load Circuit for Outputs

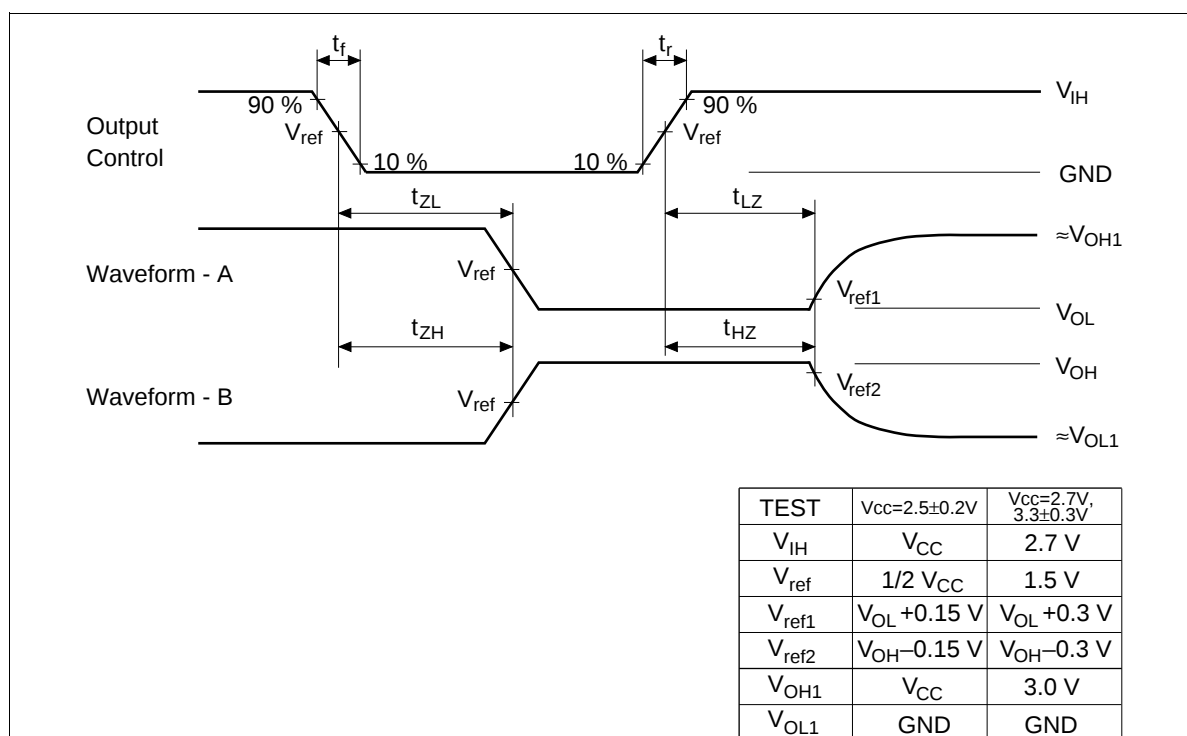
Symbol	$V_{CC}=2.5\pm0.2\text{ V}$	$V_{CC}=2.7\text{ V},$ $3.3\pm0.3\text{ V}$
t_{PLH}/t_{PHL}	OPEN	OPEN
t_{ZH}/t_{HZ}	GND	GND
t_{ZL}/t_{LZ}	$2 \times V_{CC}$	6.0 V

Note: 1. C_L includes probe and jig capacitance.

Waveforms – 1



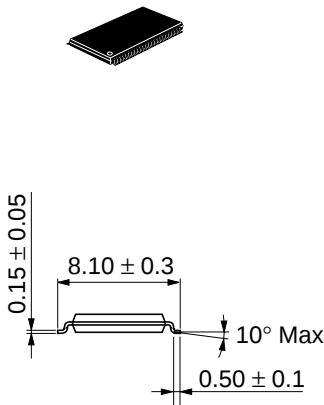
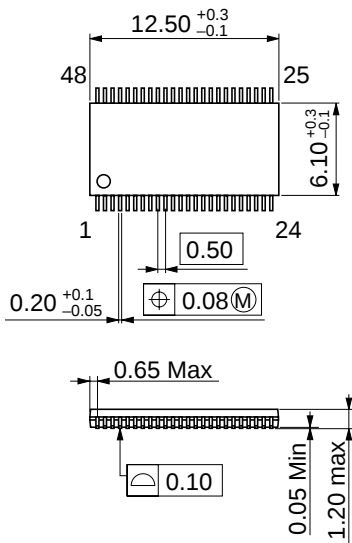
Waveforms – 2



- Notes:
1. All input pulses are supplied by generators having the following characteristics :
 $PRR \leq 10 \text{ MHz}$, $Z_o = 50 \Omega$, $t_r \leq 2.0 \text{ ns}$, $t_f \leq 2.0 \text{ ns}$. ($V_{CC} = 2.5\pm0.2 V$)
 $PRR \leq 10 \text{ MHz}$, $Z_o = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$. ($V_{CC} = 2.7 V, 3.3\pm0.3 V$)
 2. Waveform – A is for an output with internal conditions such that the output is low except when disabled by the output control.
 3. Waveform – B is for an output with internal conditions such that the output is high except when disabled by the output control.
 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit : mm



Hitachi code	TTP-48DC
EIAJ code	—
JEDEC code	—

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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